## MUN5130DW1, NSBA113EDXV6

## **Dual PNP Bias Resistor Transistors R1 = 1 k\Omega, R2 = 1 k\Omega**

## PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

## Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

(T<sub>A</sub> = 25°C, common for Q1 and Q2, unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	10	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	10	Vdc

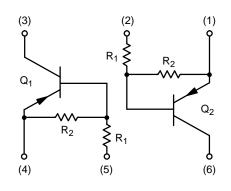
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



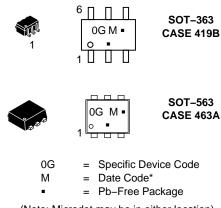
## **ON Semiconductor®**

www.onsemi.com

## **PIN CONNECTIONS**



## MARKING DIAGRAMS



(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MUN5130DW1T1G	SOT-363 (Pb-Free)	3000 / Tape & Reel
NSBA113EDXV6T1G	SOT–563 (Pb–Free)	4000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## MUN5130DW1, NSBA113EDXV6

## THERMAL CHARACTERISTICS

	Characteristic	Symbol	Max	Unit
MUN5130DW1 (SOT-363) On	e Junction Heated			
$\begin{array}{l} \mbox{Total Device Dissipation} \\ T_A = 25^\circ C \qquad (Note 1) \\ (Note 2) \\ \mbox{Derate above } 25^\circ C \\ (Note 2) \end{array}$	(Note 1)	PD	187 256 1.5 2.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	670 490	°C/W
MUN5130DW1 (SOT-363) Bo	th Junction Heated (Note 3)			
$\begin{array}{l} \mbox{Total Device Dissipation} \\ T_A = 25^\circ C \qquad (Note 1) \\ (Note 2) \\ \mbox{Derate above } 25^\circ C \\ (Note 2) \end{array}$	(Note 1)	PD	250 385 2.0 3.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	R <sub>θJA</sub>	493 325	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	R <sub>θJL</sub>	188 208	°C/W
Junction and Storage Temper	ature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
NSBA113EDXV6 (SOT-563)	Dne Junction Heated			
Total Device Dissipation $T_A = 25^{\circ}C$ (Note 1) Derate above 25^{\circ}C	(Note 1)	PD	357 2.9	m₩ mW/°C
Thermal Resistance, Junction to Ambient	(Note 1)	R <sub>θJA</sub>	350	°C/W
NSBA113EDXV6 (SOT-563) I	Both Junction Heated (Note 3)			
Total Device Dissipation $T_A = 25^{\circ}C$ (Note 1) Derate above $25^{\circ}C$	(Note 1)	PD	500 4.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1)	R <sub>θJA</sub>	250	°C/W
Junction and Storage Temper	ature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

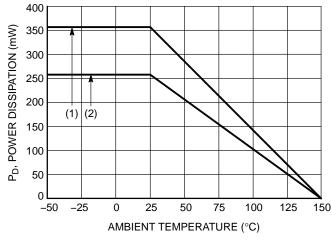
FR-4 @ Minimum Pad.
 FR-4 @ 1.0 x 1.0 Inch Pad.
 Both junction heated values assume total power is sum of two equally powered channels.

## MUN5130DW1, NSBA113EDXV6

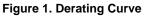
ELECTRICAL CHARACTERISTICS ( $T_A = 2$	5°C, common for Q <sub>1</sub> and Q <sub>2</sub> , unless otherwise noted)
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Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Base Cutoff Current ( $V_{CB} = 50 \text{ V}, I_E = 0$ )	I <sub>CBO</sub>	_	_	100	nAdc
Collector–Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I <sub>CEO</sub>	_	_	500	nAdc
Emitter–Base Cutoff Current ( $V_{EB} = 6.0 \text{ V}, I_C = 0$ )	I <sub>EBO</sub>	_	_	4.3	mAdc
Collector–Base Breakdown Voltage $(I_C = 10 \ \mu A, I_E = 0)$	V <sub>(BR)CBO</sub>	50	_	-	Vdc
Collector–Emitter Breakdown Voltage (Note 4) $(I_C = 2.0 \text{ mA}, I_B = 0)$	V <sub>(BR)CEO</sub>	50	_	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 4) ( $I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$ )	h <sub>FE</sub>	3.0	5.0	-	
Collector–Emitter Saturation Voltage (Note 4) $(I_C = 10 \text{ mA}, I_B = 5.0 \text{ mA})$	V <sub>CE(sat)</sub>	_	_	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0 \text{ V}, I_C = 100 \mu \text{A}$ )	V <sub>i(off)</sub>	_	1.3	-	Vdc
Input Voltage (on) ( $V_{CE} = 0.2 \text{ V}, I_{C} = 20 \text{ mA}$ )	V <sub>i(on)</sub>	_	1.7	-	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 2.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	_	_	0.2	Vdc
Output Voltage (off) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 0.05 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	_	-	Vdc
Input Resistor	R1	0.7	1.0	1.3	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	0.8	1.0	1.2	

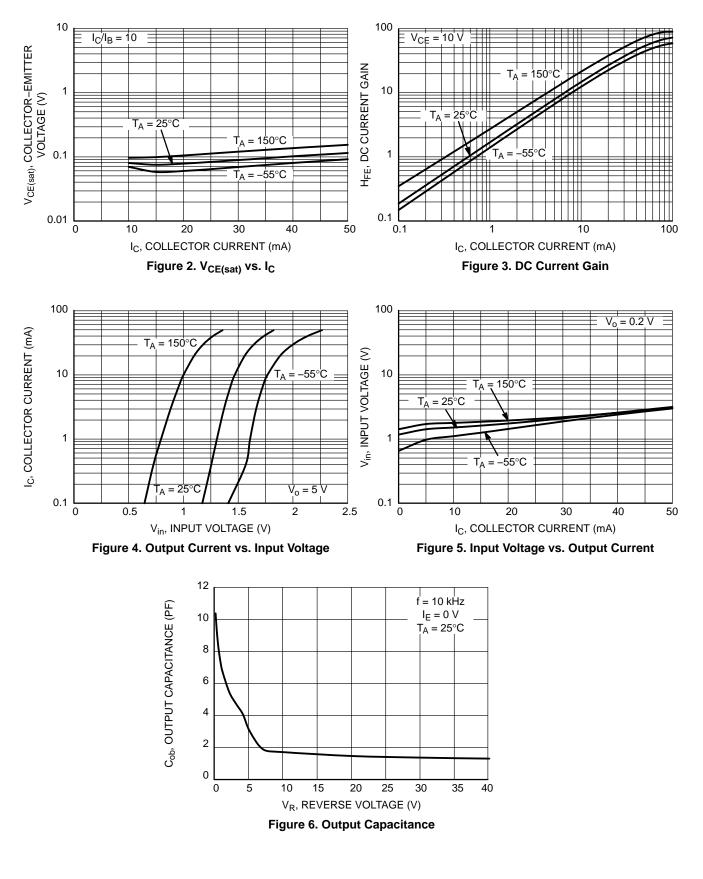
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle  $\leq 2\%$ .



(1) SOT-363; 1.0 x 1.0 inch Pad (2) SOT-563; Minimum Pad

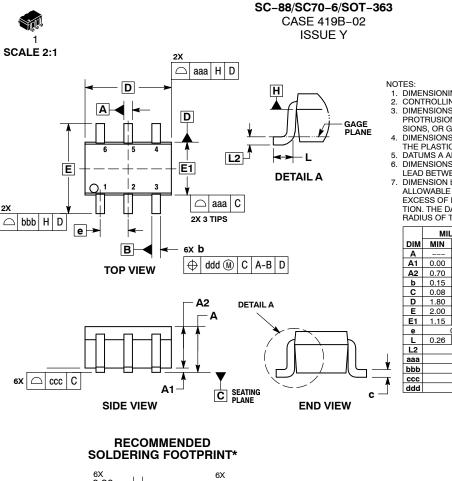


## MUN5130DW1, NSBA113EDXV6



# **NSEM**

DATE 11 DEC 2012



6X 0.30 0.66 2 50 0.65 PITCH DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  CONTROLLING DIMENSION MILLIMETERS
- CONTROLLING DIMENSION: MILLIMETERS. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
- PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRU-SIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. SIONS, OH GATE BUHHS SHALL NOT EXCEED 0.20 PEH END. DIMENSIONS D AND ET AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H. DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS 5 AND 6 APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS				INCHES	3
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
Е	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е	(	0.65 BS	С	0	.026 BS	С
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			(	0.006 BS	SC
aaa	0.15				0.006	
bbb	0.30				0.012	
ccc	0.10				0.004	
ddd		0.10			0.004	

#### GENERIC **MARKING DIAGRAM\***



XXX = Specific Device Code

- Μ = Date Code\*
- = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

## **STYLES ON PAGE 2**

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#### SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y

## DATE 11 DEC 2012

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13:	STYLE 14:	STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:
PIN 1. ANODE	PIN 1. VREF	PIN 1. ANODE 1	PIN 1. BASE 1	PIN 1. BASE 1	PIN 1. VIN1
2. N/C	2. GND	2. ANODE 2	2. EMITTER 2	2. EMITTER 1	2. VCC
3. COLLECTOR	3. GND	3. ANODE 3	3. COLLECTOR 2	3. COLLECTOR 2	3. VOUT2
4. EMITTER	4. IOUT	4. CATHODE 3	4. BASE 2	4. BASE 2	4. VIN2
5. BASE	5. VEN	5. CATHODE 2	5. EMITTER 1	5. EMITTER 2	5. GND
6. CATHODE	6. VCC	6. CATHODE 1	6. COLLECTOR 1	6. COLLECTOR 1	6. VOUT1
STYLE 19:	STYLE 20:	STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:
PIN 1. I OUT	PIN 1. COLLECTOR	PIN 1. ANODE 1	PIN 1. D1 (i)	PIN 1. Vn	PIN 1. CATHODE
2. GND	2. COLLECTOR	2. N/C	2. GND	2. CH1	2. ANODE
3. GND	3. BASE	3. ANODE 2	3. D2 (i)	3. Vp	3. CATHODE
4. V CC	4. EMITTER	4. CATHODE 2	4. D2 (c)	4. N/C	4. CATHODE
5. V EN	5. COLLECTOR	5. N/C	5. VBUS	5. CH2	5. CATHODE
6. V REF	6. COLLECTOR	6. CATHODE 1	6. D1 (c)	6. N/C	6. CATHODE
STYLE 25:	STYLE 26:	STYLE 27:	STYLE 28:	STYLE 29:	STYLE 30:
PIN 1. BASE 1	PIN 1. SOURCE 1	PIN 1. BASE 2	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. SOURCE 1
2. CATHODE	2. GATE 1	2. BASE 1	2. DRAIN	2. ANODE	2. DRAIN 2
3. COLLECTOR 2	3. DRAIN 2	3. COLLECTOR 1	3. GATE	3. COLLECTOR	3. DRAIN 2
4. BASE 2	4. SOURCE 2	4. EMITTER 1	4. SOURCE	4. EMITTER	4. SOURCE 2
5. EMITTER	5. GATE 2	5. EMITTER 2	5. DRAIN	5. BASE/ANODE	5. GATE 1
6. COLLECTOR 1	6. DRAIN 1	6. COLLECTOR 2	6. DRAIN	6. CATHODE	6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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NDTES:

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MILLIMETERS

NDM.

0.55

0.22

0.13

1.60

1.20

0.50 BSC

0.20

1.60

MAX.

0.60

0.27

0.18

1.70

1.30

0.30

1.70

SIDE VIEW

MIN.

0.50

0.17

0.08

1.50

1.10

0.10

1.50



SOT-563, 6 LEAD CASE 463A ISSUE H

DATE 26 JAN 2021

SCALE 4:1

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

А

DIM

Α

b

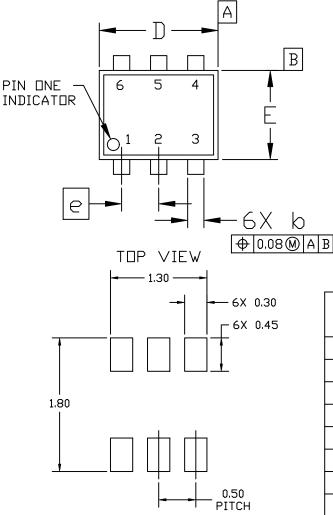
С

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RECOMMENDED MOUNTING FOOTPRINT\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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## DUSEM

#### SOT-563, 6 LEAD CASE 463A ISSUE H

DATE 26 JAN 2021

GENERIC	
MARKING DIAGRAM*	

		1
	XX M•	
4	0	
1		

XX = Specific Device Code

M = Month Code

= Pb-Free Package .

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. EMITTER 1	PIN 1. EMITTER 1	PIN 1. CATHIDE 1
2. BASE 1	2. EMITTER 2	2. CATHIDE 1
3. COLLECTOR 2	3. BASE 2	3. ANIDE/ANIDE 2
4. EMITTER 2	4. COLLECTOR 2	4. CATHIDE 2
5. BASE 2	5. BASE 1	5. CATHIDE 2
6. COLLECTOR 1	6. COLLECTOR 1	6. ANIDE/ANIDE 1
STYLE 4:	STYLE 5:	STYLE 6:
PIN 1. COLLECTOR	PIN 1. CATHODE	PIN 1. CATHIDE
2. COLLECTOR	2. CATHODE	2. ANIDE
3. BASE	3. ANODE	3. CATHIDE
4. EMITTER	4. ANODE	4. CATHIDE
5. COLLECTOR	5. CATHODE	5. CATHIDE
6. COLLECTOR	6. CATHODE	6. CATHIDE
STYLE 7:	STYLE 8:	STYLE 9:
PIN 1. CATHODE	PIN 1. DRAIN	PIN 1. SDURCE 1
2. ANODE	2. DRAIN	2. GATE 1
3. CATHODE	3. GATE	3. DRAIN 2
4. CATHODE	4. SEURCE	4. SDURCE 2
5. ANODE	5. DRAIN	5. GATE 2
6. CATHODE	6. DRAIN	6. DRAIN 1
STYLE 10: PIN 1. CATHIDE 1 2. N/C 3. CATHIDE 2 4. ANIDE 2 5. N/C 6. ANIDE 1	STYLE 11: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	

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